IN THE CLAIMS

1. (Original) A semiconductor device comprising:

a semiconductor substrate;

a gate line crossing over the semiconductor substrate; and

a protecting pattern covering ends of the gate line.

2. (Original) The semiconductor device of claim 1, wherein the protecting pattern is formed of a material chosen from the group consisting of silicon nitride and silicon oxide.

3. (Original) The semiconductor device of claim 1, further comprising a spacer covering sidewalls of the gate line and interposed between the gate line and the protecting pattern at the ends of the gate line.

4. (Original) The semiconductor device of claim 3, wherein the spacer is formed of a material chosen from the group consisting of silicon nitride and silicon oxide.

5. (Original) The semiconductor device of claim 1, wherein the gate line comprises an oxide pattern and a conductive pattern that are sequentially stacked on the semiconductor substrate.

6. (Original) The semiconductor device of claim 5, wherein the conductive pattern is formed of a metal selected from the group consisting of tungsten, copper, and aluminum.

7. (Withdrawn) A method of forming a semiconductor device, comprising:

forming a gate line at a semiconductor substrate;

forming a spacer covering sidewalls of the gate line; and

forming a protecting pattern covering ends of the gate line.

8. (Withdrawn) The method of claim 7, wherein forming a spacer and forming a protecting pattern comprises forming the spacer and forming the protecting pattern simultaneously, wherein the spacer and the protecting pattern are formed of a same material.

9. (Withdrawn) The method of claim 8, wherein the same material is chosen from the group consisting of silicon nitride and silicon oxide.

10. (Withdrawn) The method of claim 7, wherein forming the gate line comprises:

sequentially stacking an oxide layer and a conductive layer on the semiconductor substrate; and

sequentially patterning the conductive layer and the oxide layer.

11. (Withdrawn) The method of claim 10, wherein the conductive layer is formed of a metal selected from the group consisting of tungsten, copper, and aluminum.

12. (New) A semiconductor device comprising:

a semiconductor substrate;

a gate line crossing over the semiconductor substrate;

a protecting pattern covering ends of the gate line; and

a spacer covering sidewalls of the gate line and interposed between the gate line and the protecting pattern at the ends of the gate line.

13. (New) The device of claim 12, wherein the spacer is formed of a material chosen from the group consisting of silicon nitride and silicon oxide.